L Number	Hits	Search Text	DB	Time stamp
1	2930000	memory or storage	USPAT;	2004/10/17 15:59
_			US-PGPUB;	
			EPO; JPO;	
ļ		·	DERWENT	
2	28893	(memory or storage) and resistance with cell	USPAT;	2004/10/17 16:01
-	20033	(memory or storage) and resistance was cen	US-PGPUB;	200 1, 20, 2, 20102.
			EPO; JPO;	
			DERWENT	
3	13957	(memory or storage) and resistive with (cell or element or	USPAT;	2004/10/17 16:02
Ĭ	1000,	unit)	US-PGPUB;	2001/10/17 10:02
			EPO; JPO;	
			DERWENT	
4	41173	((memory or storage) and resistance with cell) ((memory or	USPAT;	2004/10/17 16:02
'	111/3	storage) and resistive with (cell or element or unit))	US-PGPUB;	200 1/10/17 10:02
		Storage) and resistive with (cen or element of unity)	EPO; JPO;	
			DERWENT	
5	3181	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:10
]	5101	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2001/10/17 10:10
		select\$5 adj2 (transistor or element)	EPO; JPO;	
		Science 3 days (dansistor of element)	DERWENT	
6	833	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:03
	033	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	200 1/10/17 10:05
		select\$5 adj2 (transistor or element)) and (mram or	EPO; JPO;	
		magnetic)	DERWENT	
7	1301	(((memory or storage) and resistance with cell) ((memory		2004/10/17 16:04
'	1501	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2004/10/17 10:04
	,	select\$5 with diode	EPO; JPO;	
		, selectips with aloue	DERWENT	ł
8	373	(((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:09
`	3/3	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2001/10/17 10:05
		select\$5 adj2 (transistor or element)) and (mram or	EPO; JPO;]
		magnetic)) and 365/\$.ccls.	DERWENT	
10	39	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:17
10	33	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2001/10/17 10:17
		variable adj resistive) and select\$5 adj2 (transistor or	EPO; JPO;	
		element)	DERWENT	
9	162	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:14
-		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	
		variable adj resistive	EPO; JPO;	
		,	DERWENT	
11	3439	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:17
		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	
		resist\$6 with diode	EPO; JPO;	
		·	DERWENT	
12	1040	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:17
_		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	, ,
		resist\$6 with diode) and cell with diode	EPO; JPO;	
		•	DERWENT	
13	425	(((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:18
		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	
		resist\$6 with diode) and cell with diode) and 365/\$.ccls.	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT	

L Number	Hits	Search Text	DB	Time stamp
1	2930000	memory or storage	USPAT;	2004/10/17 15:59
_	250000	manary of storage	US-PGPUB;	2001/10/17 10:05
			EPO; JPO;	
i			DERWENT	
2	28893	(memory or storage) and resistance with cell	USPAT;	2004/10/17 16:01
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	• .,
		•	EPO; JPO;	
			DERWENT	
3	13957	(memory or storage) and resistive with (cell or element or	USPAT;	2004/10/17 16:02
		unit)	US-PGPUB;	
			EPO; JPO;	
	==		DERWENT	
4	41173	((memory or storage) and resistance with cell) ((memory or	USPAT;	2004/10/17 16:02
		storage) and resistive with (cell or element or unit))	US-PGPUB;	
			EPO; JPO;	
5	3181	///mamon, or storage) and resistance with cell \//memon	DERWENT	2004/10/17 16:10
3	2101	(((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and	USPAT; US-PGPUB;	2004/10/17 16:10
		select\$5 adj2 (transistor or element)	EPO; JPO;	
		Science adjz (dansistor or element)	DERWENT	
6	833	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:03
		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2001/10/17 10:03
		select\$5 adj2 (transistor or element)) and (mram or	EPO; JPO;	•
		magnetic)	DERWENT	
7	1301	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:04
		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	, ,
		select\$5 with diode	EPO; JPO;	,
			DERWENT	
8	373	(((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:09
		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	
		select\$5 adj2 (transistor or element)) and (mram or	EPO; JPO;	
		magnetic)) and 365/\$.ccls.	DERWENT	
9	162	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:10
]		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	
1		variable adj resistive	EPO; JPO; DERWENT	
10	39	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:12
10] 39	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2004/10/17 10:12
		variable adj resistive) and select\$5 adj2 (transistor or	EPO; JPO;	
		element)	DERWENT	,
		Comony	DEIXITEIT	l